

Silicon PNP Power Transistors

2SB1034

DESCRIPTION

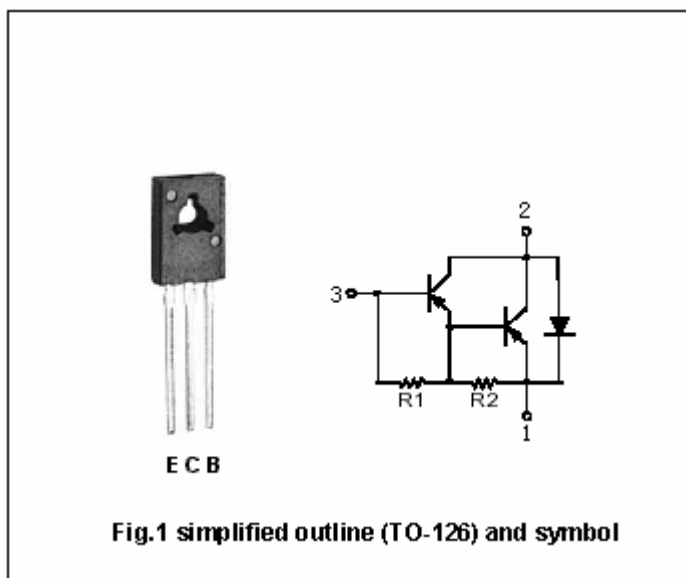
- With TO-126 package
- Low collector saturation voltage
- High DC current gain
- DARLINGTON

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-80	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-80	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-8	V
I <sub>C</sub>	Collector current (DC)		-2	A
I <sub>B</sub>	Base current (DC)		-0.5	A
P <sub>C</sub>	Total power dissipation	T <sub>C</sub> =25°C	15	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-80			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1A ; I <sub>B</sub> =-1mA			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-1A ; I <sub>B</sub> =-1mA			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V ; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-8V ; I <sub>C</sub> =0			-4	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V	2000			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1MHz		30		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-2V		50		MHz

## Switching times

t <sub>on</sub>	Turn-on time	R <sub>L</sub> =30Ω I <sub>B1</sub> =I <sub>B2</sub> =1mA V <sub>CC</sub> =-30V		0.4		μs
t <sub>s</sub>	Storage time			2.0		μs
t <sub>f</sub>	Fall time			0.4		μs

PACKAGE OUTLINE

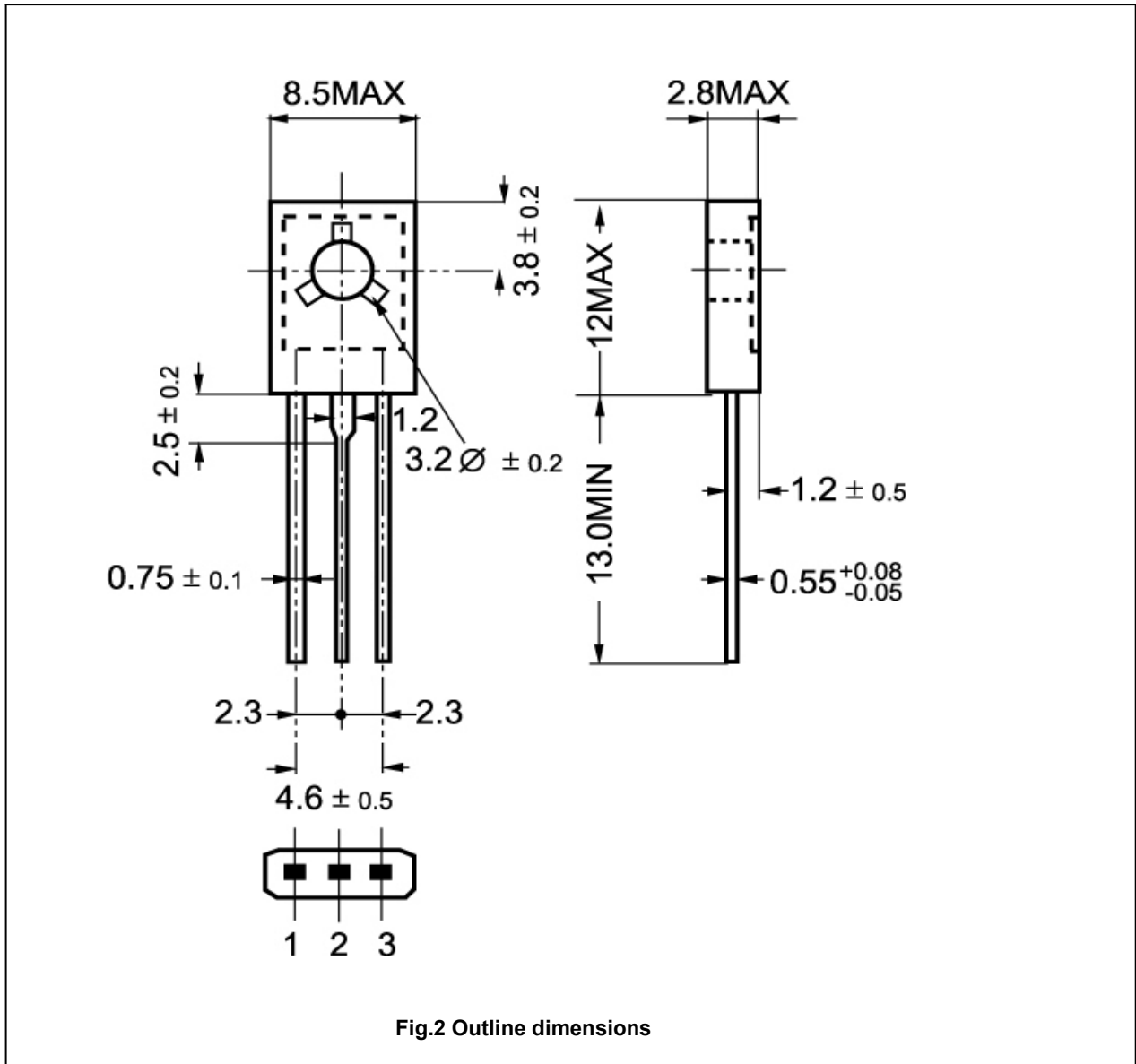


Fig.2 Outline dimensions